/ Descriptions

TO-252	PNP	Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

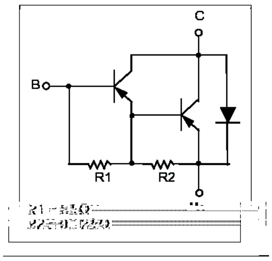
TIP122D

Complement to TIP122D.

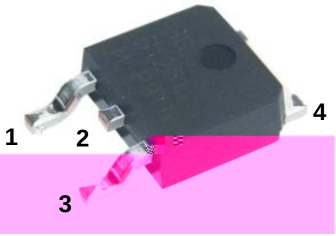
/ Applications

Medium power linear switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

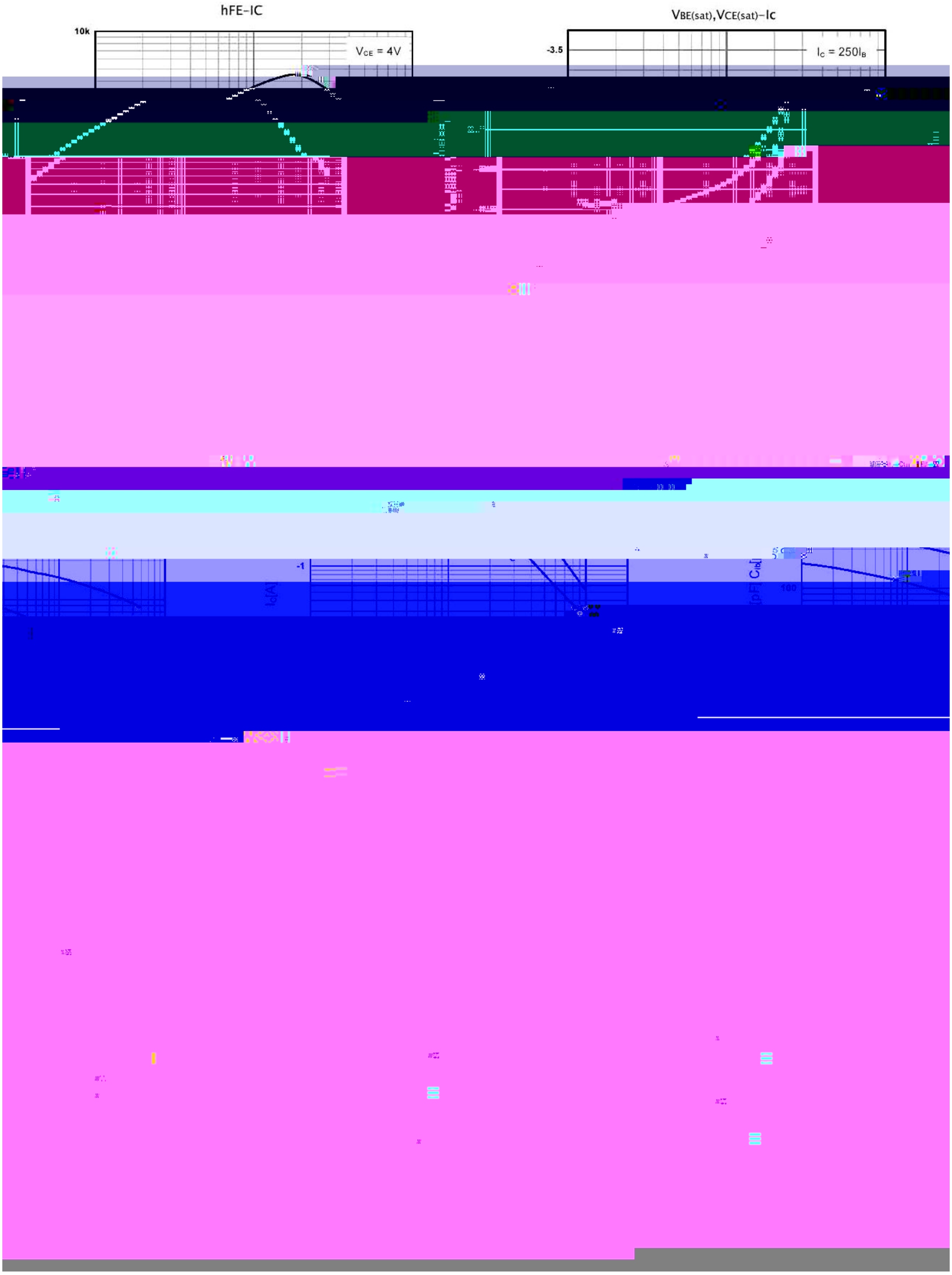
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Power Dissipation	$P_C(T_C=25\ )$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

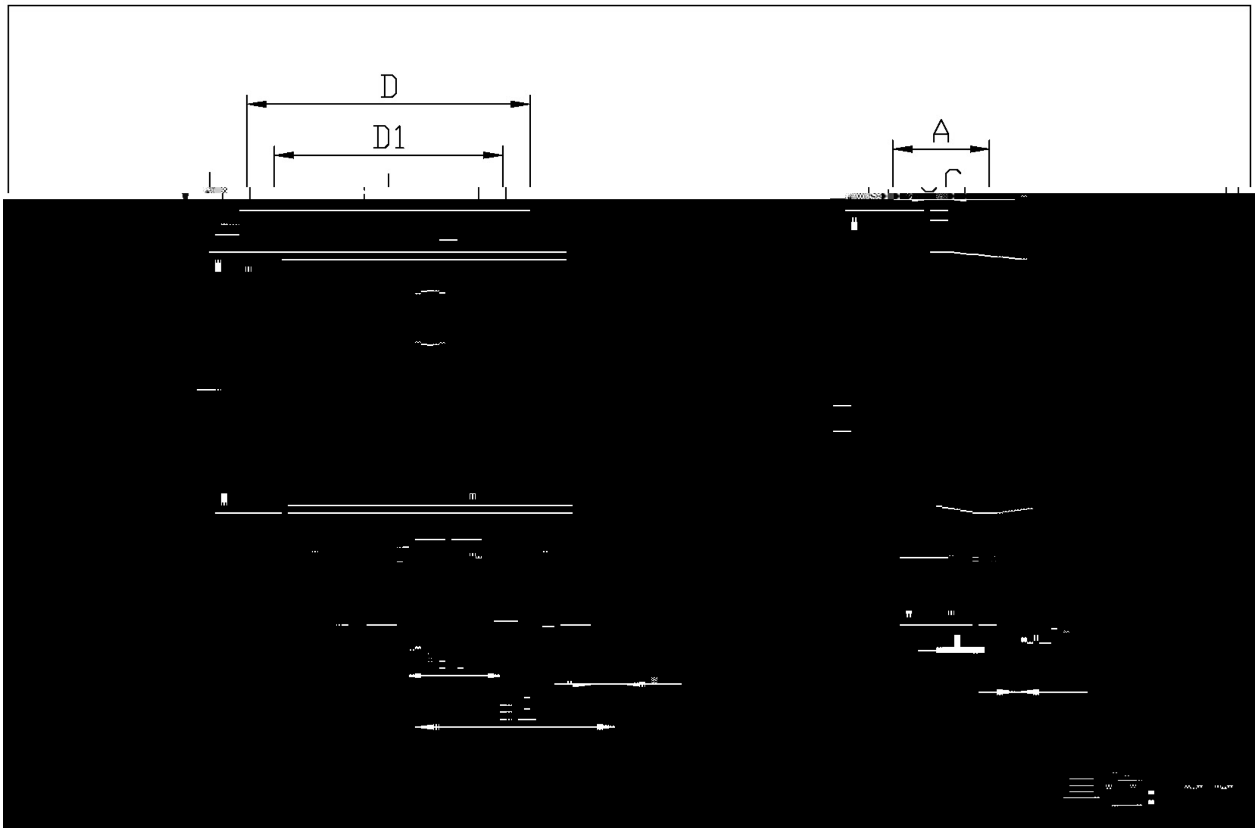
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-100mA I_B=0	-100			V
Collector Cut-Off Current	I_{CBO}	V_{CE}=-50V I_B=0			-2.0	mA
Collector Cut-Off Current	I_{CEO}	V_{CB}=-100V I_E=0			-1.0	mA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-2.0	mA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-3.0V I_C=-0.5A	1000			
	$h_{FE(2)}$	V_{CE}=-3.0V I_C=-3.0A	1000			
Collector to Emitter Saturation Voltage	$V_{CE(sat)\ (1)}$	I_C=-3.0A I_B=-12mA			-2.0	V
	$V_{CE(sat)\ (2)}$	I_C=-5.0A I_B=-20mA			-4.0	V
Base to Emitter Voltage	V_{BE}	I_C=-3.0A V_{CE}=-3.0V			-2.5	V
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=0.1MHz			300	pF

/ Electrical Characteristic Curve



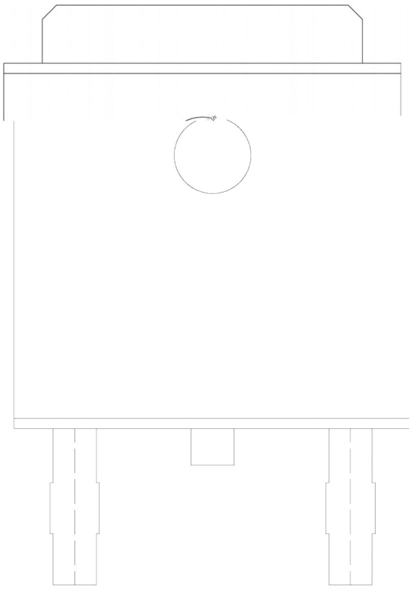
/ Package Dimensions



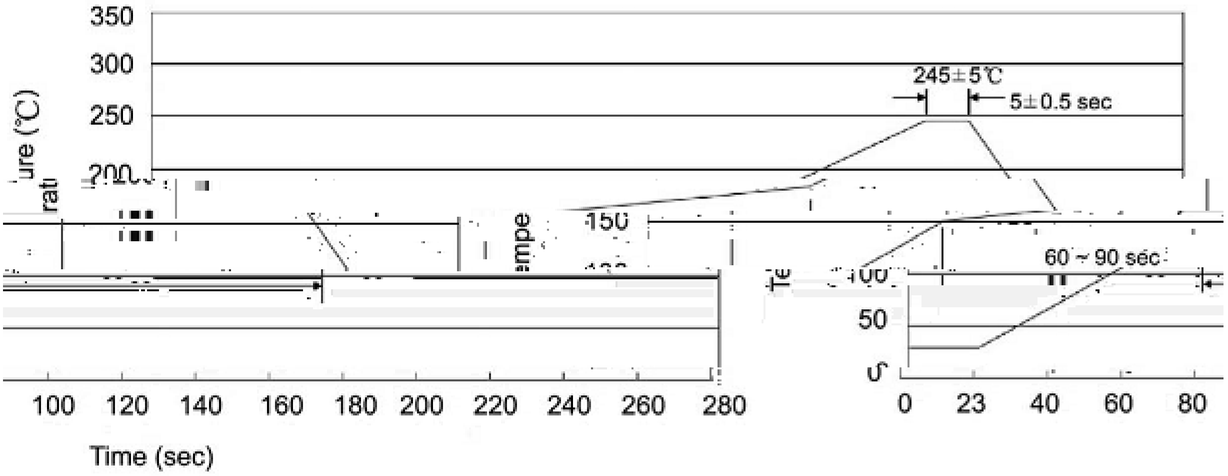
Symbol	Min	Max	Symbol	Min	Max
[illegible]	[illegible]	[illegible]	[illegible]	[illegible]	[illegible]
D1	5.10	5.50	K	0.00	0.10

TO-252

/ Marking Instructions



(   ) /   Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

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